

FDP6670AL/FDB6670AL

N-Channel Logic Level PowerTrench[®] MOSFET

General Description

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

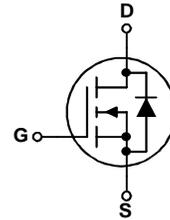
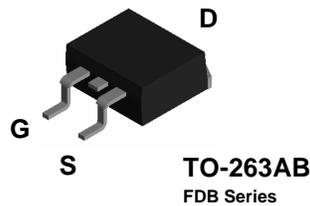
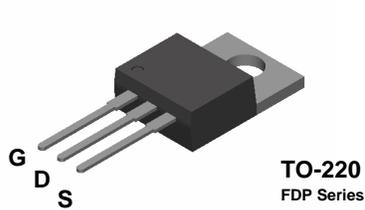
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

Features

- 80 A, 30 V $R_{DS(ON)} = 6.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 8.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Critical DC electrical parameters specified at elevated temperature
- High performance trench technology for extremely low $R_{DS(ON)}$
- 175°C maximum junction temperature rating



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1)	80	A
	– Pulsed (Note 1)	240	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	68	W
		0.45	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-65 to +175	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.2	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB6670AL	FDB6670AL	13"	24mm	800 units
FDP6670AL	FDP6670AL	Tube	n/a	45

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Drain-Source Avalanche Ratings (Note 1)

W_{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15\text{ V}, I_D = 80\text{ A}$			114	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				80	A

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		24		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 37\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 40\text{ A}, T_J = 125^\circ\text{C}$		5.2 6.5 7.2	6.5 8.5 9.7	m Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$	80			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 40\text{ A}$		115		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$		2440		pF
C_{oss}	Output Capacitance	$f = 1.0\text{ MHz}$		580		pF
C_{riss}	Reverse Transfer Capacitance			250		pF
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		1.4		Ω

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A},$		13	23	ns
t_r	Turn-On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		13	23	ns
$t_{d(off)}$	Turn-Off Delay Time			42	68	ns
t_f	Turn-Off Fall Time			15	27	ns
Q_g	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 40\text{ A},$		24	33	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 5\text{ V}$		7		nC
Q_{gd}	Gate-Drain Charge			9		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current				80	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 40\text{ A}$ (Note 1)		0.9	1.3	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 40\text{ A},$		34		nS
Q_{rr}	Diode Reverse Recovery Charge	$dI_F/dt = 100\text{ A}/\mu\text{s}$		24		nC

Notes:

1. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

Typical Characteristics

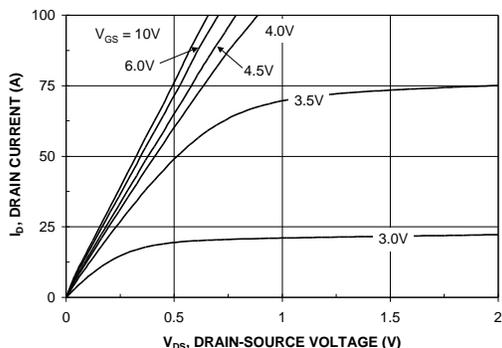


Figure 1. On-Region Characteristics.

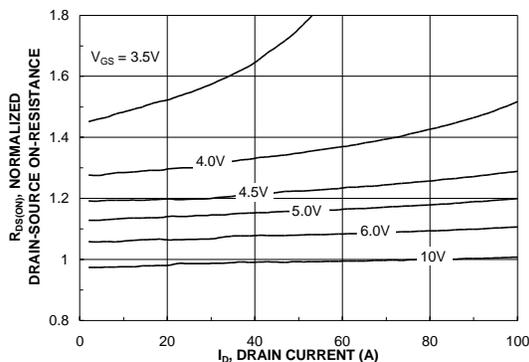


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

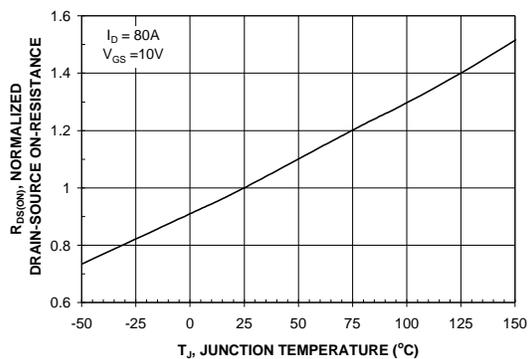


Figure 3. On-Resistance Variation with Temperature.

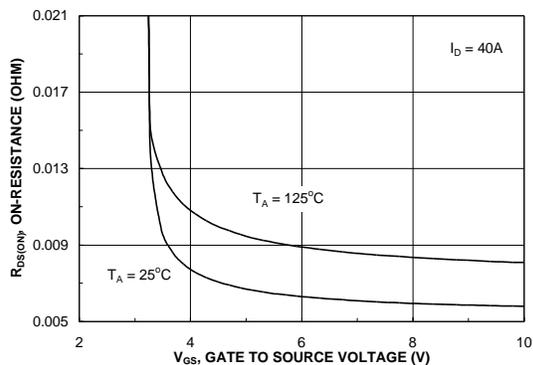


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

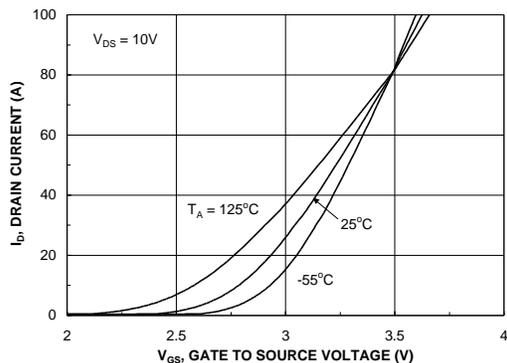


Figure 5. Transfer Characteristics.

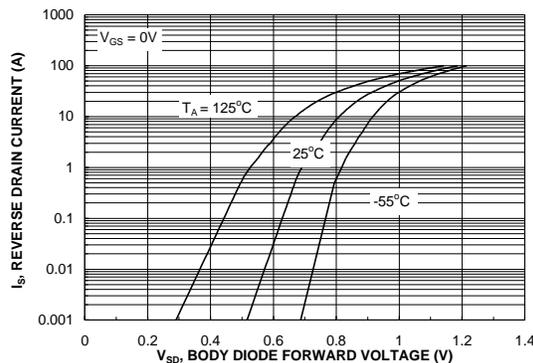


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.